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1. (Amended) A group III nitride compound semiconductor light-emitting device comprising:

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a light-emitting layer of a multilayer quantum well structure composed of alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein said n-layer clad layer is made thicker than each of said barrier layer and the thickness is in a range of 100 Å to 500 Å,

wherein said n-clad layer is formed of a material substantially the same as said barrier layers.

See the attached Appendix for the changes made to effect the above claims.